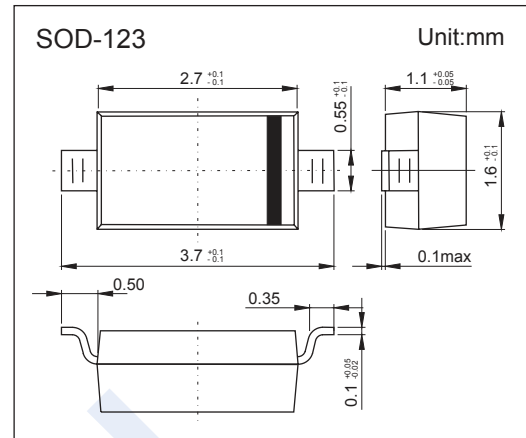


Switching Diodes

L1N4148WT1G

■ Features

- Fast Switching Speed
- For General Purpose Switching Applications.
- High Conductance
- Surface Mount Package Ideally Suited for Automatic Insertion
- Pb-Free package is available

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V
Peak Repetitive Reverse Voltage	V _{RRM}	75	
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
RMS Reverse Voltage	V _{R(RMS)}	53	
Average Rectified Output Current	I _o	200	mA
Repetitive Rectified Output Current	I _{FM}	300	
Non-Repetitive Peak Forward Surge Current t=1us t=1s	I _{FSM}	2	A
		1	
Power Dissipation	P _D	425	mW
Thermal Resistance Junction to Ambient	R _{θJA}	290	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-65 to 150	

Switching Diodes

L1N4148WT1G

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100\text{ }\mu\text{A}$	100			V
Forward voltage	V_F	$I_F = 1\text{ mA}$			0.715	
		$I_F = 10\text{ mA}$			0.855	
		$I_F = 50\text{ mA}$			1	
		$I_F = 150\text{ mA}$			1.25	
Reverse voltage leakage current	I_R	$V_R = 75\text{ V}$			2.5	μA
		$V_R = 75\text{ V}, T_J = 150^\circ\text{C}$			50	
		$V_R = 20\text{ V}$			25	nA
		$V_R = 25\text{ V}, T_J = 25^\circ\text{C}$			30	μA
Capacitance between terminals	C_T	$V_R = 0\text{ V}, f = 1\text{ MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$			4	ns

■ Marking

Marking	T4
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■ Typical Characteristics

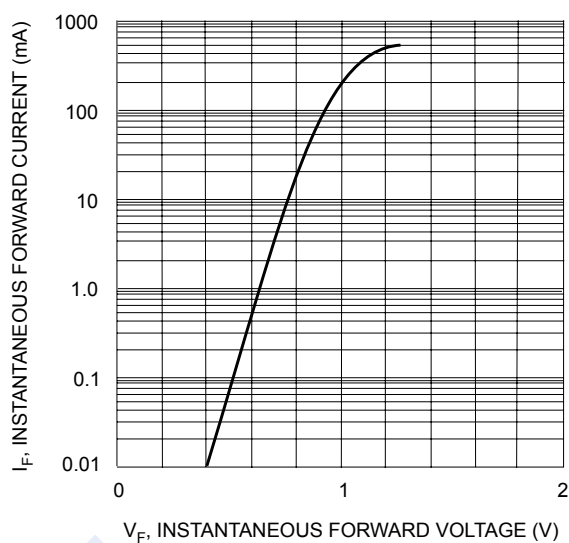


Fig. 1 Forward Characteristics

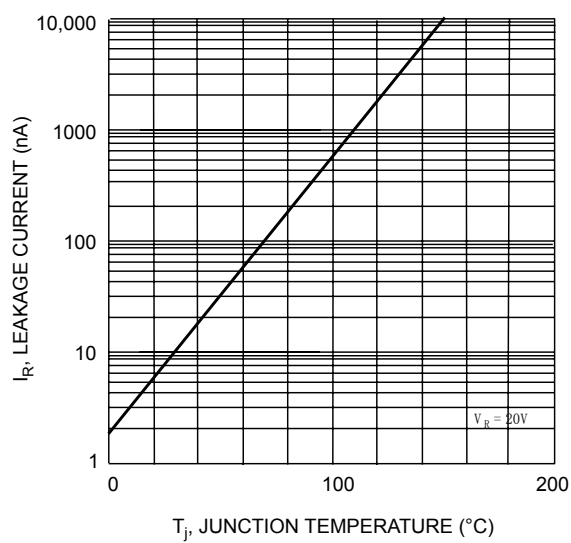


Fig. 2 Leakage Current vs Junction Temperature